

S-Band Radar 50Ω Transistor - GaN

- GaN on SiC HEMT Technology
- $P_{OUT-PK} = 135W @ 300us/10%/46V$
- 3.1-3.5GHz Instantaneous Operating Frequency Range
- 50Ω Internally Impedance Matched Device
- Depletion Mode Device
- Negative Gate Voltage and Bias Sequencing Required
- Metal Based Package Sealed With Ceramic-Epoxy Lid
- Gold Metallization System: Chip - Wire Bond - Package
- Package Size Bolt Down: W=0.800"(20.32mm), L=0.400"(10.16mm)
- Package Size S(earless): W=0.400"(10.16mm), L=0.400"(10.16mm)
- 100% High Power RF Tested in Broadband RF Test Fixture



PARAMETER	SYM	MIN	TYP	MAX	UNITS	TEST CONDITIONS
DC ELECTRICAL SPECIFICATIONS						
Drain Leakage Current	I_{D-OFF}	--	1.0	--	mA	$V_{DS}=50V, V_{GS}=-8V, T_{F1}, S1$
Gate Threshold Voltage	V_{GS-TH}	--	-2.8	--	V	$V_{DS}=5V, I_D=100mA, T_{F1}, S1$
RF ELECTRICAL SPECIFICATIONS						
Input Return Loss	IRL	-18	-10	-7	dB	POUT1, V1, I_{DQ1} , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Power Gain	Gp	12.5	13.5	15.5	dB	POUT1, V1, I_{DQ1} , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Drain Efficiency	N_D	50	55	75	%	POUT1, V1, I_{DQ1} , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Pulse Amplitude Droop	D	-0.80	-0.40	+0.20	dB	POUT1, V1, I_{DQ1} , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Delta Inter-pulse Insertion Phase	DIP	-30	--	+30	DEG	POUT1, V1, I_{DQ1} , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Load Mismatch Stability	VSWR-S	3:1	--	--	--	POUT1, V1, I_{DQ1} , PW1, DF1, F1, F2, F3, $T_{F1}, S1$
Load Mismatch Tolerance	VSWR-T	8:1	--	--	--	POUT1, V1, I_{DQ1} , PW1, DF1, F1, F2, F3, $T_{F1}, S1$

PARAMETER	SYM	MIN	NOM	MAX	UNITS	TEST CONDITIONS
DC & RF TEST CONDITIONS						
Output Power 1	POUT1	--	135	--	W	--
Drain Supply Voltage 1	V1	--	46.0	--	V	--
Quiescent Drain Current 1	I_{DQ1}	20	25	30	mA	--
Pulse Width 1	PW1	--	300	--	us	--
Duty Factor 1	DF1	--	10	--	%	--
Frequency 1	F1	--	3.1	--	GHz	--
Frequency 2	F2	--	3.3	--	GHz	--
Frequency 3	F3	--	3.5	--	GHz	--
Flange Temperature 1	T_{F1}	20	25	30	°C	--
Screening Level 1	S1	100	--	--	%	--

PARAMETER	SYM	MIN	MAX	UNITS	SCREEN	CONDITIONS
MAXIMUM RATINGS						
Drain-Source Voltage	V_{DS}	--	60	V	BD	$T_F = 25^\circ\text{C}$
Gate-Source Voltage	V_{GS}	-10	0	V	BD	$T_F = 25^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55	+150	$^\circ\text{C}$	BD	--
Operating Junction Temperature	T_J	-55	+200	$^\circ\text{C}$	BD	--
PROCESS SPECIFICATIONS						
DC Wafer Probe	--	--	--	--	100%	Per Integra Spec
Wafer DC, RF Qualification	--	--	--	--	Q1	Per Integra Spec
Wire Bond Strength	--	--	--	--	LM	Per Integra Spec
Pre-cap Visual Inspection	--	--	--	--	100%	Per Integra Spec
Gross Leak Test – MIL-STD-750D	--	--	--	--	100%	Method 1071.6 C
THERMAL RESISTANCE						
Peak Thermal Resistance Per Rated RF Specification	$R_{TH(JC)}$	--	0.60	$^\circ\text{C/W}$	BD	$T_F = 25^\circ\text{C}$
Peak Thermal Resistance at PW=100us/20%	$R_{TH(JC)}$	--	0.48	$^\circ\text{C/W}$	BD	$T_F = 25^\circ\text{C}$
SCREENING LEVELS						
Parameter Qualified By Design	BD	--	--	--	--	--
Parameter Qualified By 3 Pieces (min) Per Wafer	Q1	--	--	--	--	--
Parameter Qualified By Assembly Line Monitor	LM	--	--	--	--	--

RF TEST FIXTURE – 50Ω BROADBAND

- ▶ Broadband RF Test Fixture. Provides 50Ω Impedance To the Device Across the Rated Operating Frequency Range.
- ▶ Electronic CAD Drawing File Available Upon Request. Includes Circuit Dimensions and Parts List.
- ▶ Reference Design PCB: Rogers RO4350B-03011, DK=3.48.

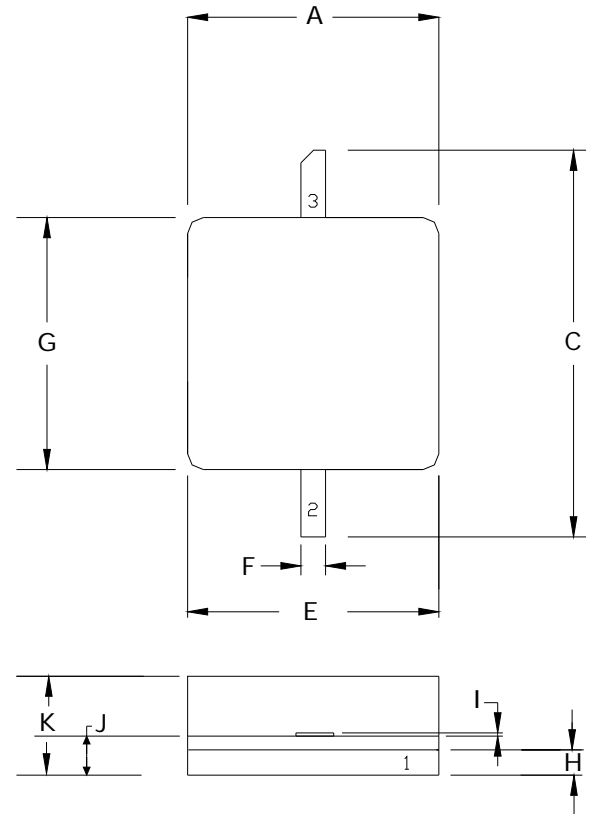
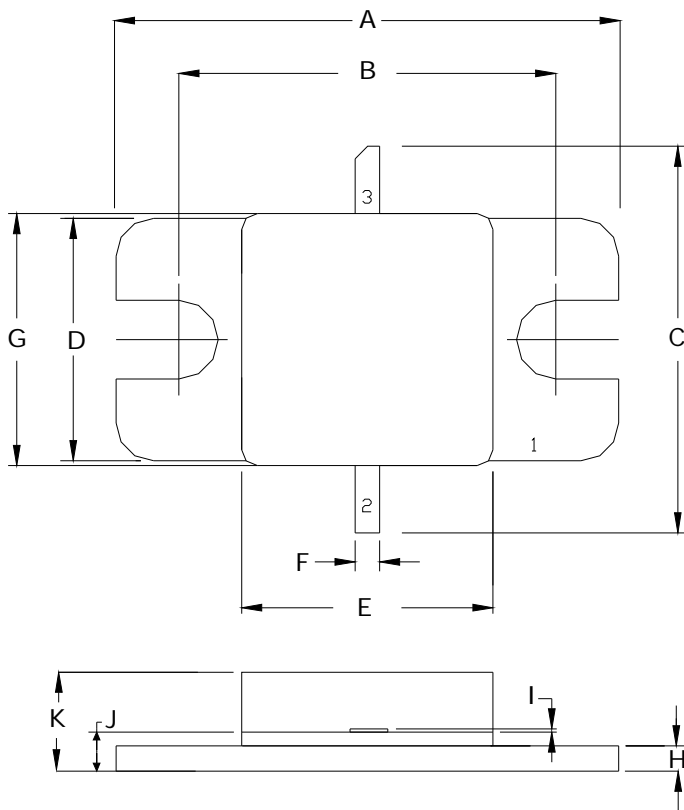
DC BIAS SEQUENCING**Turn ON GaN Device**

1. RF Power OFF
2. Set VGS = -5V (Negative Voltage to pinch off)
3. Measure VDS impedance, should be pinched off.
4. Turn ON VDD voltage.
5. Slowly increase VGS until bias current IDQ is set.
6. Turn ON RF Power

Turn OFF GaN Device

1. Turn OFF RF Power
2. Turn OFF VDD voltage
3. After VDD is discharged, set VGS = -5V
4. Turn OFF VGS voltage.

PACKAGE OUTLINE DRAWING



BOLT DOWN VERSION - IGT3135M135

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.795	0.805	20.19	20.45
B	0.595	0.605	15.11	15.37
C	0.579	0.649	14.71	16.48
D	0.380	0.390	9.65	9.91
E	0.393	0.420	9.98	10.67
F	0.034	0.044	0.86	1.12
G	0.393	0.420	9.98	10.67
H	0.035	0.045	0.89	1.14
I	0.004	0.006	0.10	0.15
J	0.055	0.069	1.40	1.75
K	0.131	0.181	3.33	4.60

'S' VERSION - IGT3135M135S

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.393	0.420	9.98	10.67
C	0.579	0.649	14.71	16.48
E	0.393	0.420	9.98	10.67
F	0.034	0.044	0.86	1.12
G	0.393	0.420	9.98	10.67
H	0.035	0.045	0.89	1.14
I	0.004	0.006	0.10	0.15
J	0.055	0.069	1.40	1.75
K	0.131	0.181	3.33	4.60

PIN SCHEDULE	
1	SOURCE
2	GATE
3	DRAIN

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1	SOURCE
2	GATE
3	DRAIN

DEFINITIONS**DATA SHEET STATUS**

Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.

MAXIMUM RATINGS

Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

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